

TOSHIBA Multi-Chip Device Silicon P-Channel MOS Type + N-Channel MOS Type

SSM6E03TU

○Power Management Switch Applications

- P-channel MOSFET and 1.8 V drive
- N-channel MOSFET and 1.5 V drive
- P-channel MOSFET and N-channel MOSFET incorporated into one package.
- Low power dissipation due to P-channel MOSFET that features low R_{DS (ON)} and low-voltage operation

Q1 Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | Symbol | Rating | Unit |
|----------------------|-----------------|--------------------------|------|
| Drain-Source voltage | V _{DS} | -20 | V |
| Gate-Source voltage | V _{GS} | ± 8 | V |
| Drain current | DC | I _D | -1.8 |
| | Pulse | I _{DP} (Note 1) | -3.6 |

Q2 Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | Symbol | Rating | Unit |
|----------------------|-----------------|--------------------------|------|
| Drain-Source voltage | V _{DS} | 20 | V |
| Gate-Source voltage | V _{GS} | ± 10 | V |
| Drain current | DC | I _D | 0.1 |
| | Pulse | I _{DP} (Note 1) | 0.2 |

Absolute Maximum Ratings (Q1, Q2 common) (Ta = 25°C)

| Characteristics | Symbol | Rating | Unit |
|---------------------------|-------------------------|------------|------|
| Drain power dissipation | P _D (Note 2) | 0.5 | W |
| Channel temperature | T _{ch} | 150 | °C |
| Storage temperature range | T _{stg} | -55 to 150 | °C |

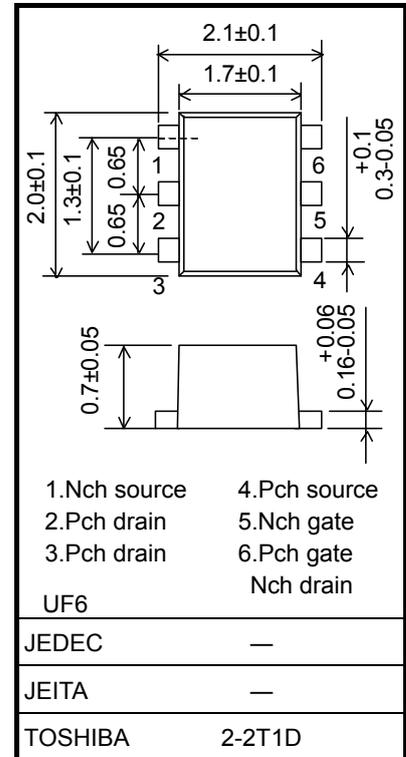
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Pulse width limited by maximum channel temperature.

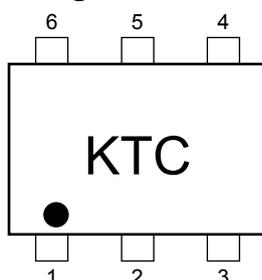
Note 2: Mounted on an FR4 board (25.4 mm × 25.4 mm × 1.6 mm, Cu pad: 645 mm²)

Unit: mm

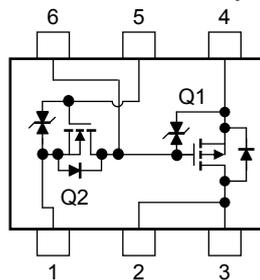


Weight: 7.0 mg (typ.)

Marking



Equivalent Circuit (top view)



Q1 Electrical Characteristics (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit | |
|--------------------------------|---------------|--|--|------|---------|---------------|----|
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $I_D = -1 \text{ mA}, V_{GS} = 0$ | -20 | — | — | V | |
| | $V_{(BR)DSX}$ | $I_D = -1 \text{ mA}, V_{GS} = +8 \text{ V}$ | -12 | — | — | | |
| Drain cutoff current | I_{DSS} | $V_{DS} = -20 \text{ V}, V_{GS} = 0$ | — | — | -10 | μA | |
| Gate leakage current | I_{GSS} | $V_{GS} = \pm 8 \text{ V}, V_{DS} = 0$ | — | — | ± 1 | μA | |
| Gate threshold voltage | V_{th} | $V_{DS} = -3 \text{ V}, I_D = -1 \text{ mA}$ | -0.3 | — | -1.0 | V | |
| Forward transfer admittance | $ Y_{fs} $ | $V_{DS} = -3 \text{ V}, I_D = -1 \text{ A}$ (Note 3) | 1.8 | 3.7 | — | S | |
| Drain-source ON-resistance | $R_{DS(ON)}$ | $I_D = -1.0 \text{ A}, V_{GS} = -4 \text{ V}$ (Note 3) | — | 105 | 144 | m Ω | |
| | | $I_D = -0.5 \text{ A}, V_{GS} = -2.5 \text{ V}$ (Note 3) | — | 138 | 180 | | |
| | | $I_D = -0.2 \text{ A}, V_{GS} = -1.8 \text{ V}$ (Note 3) | — | 190 | 335 | | |
| Input capacitance | C_{iss} | $V_{DS} = -10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$ | — | 335 | — | pF | |
| Output capacitance | C_{oss} | | — | 70 | — | | |
| Reverse transfer capacitance | C_{rss} | | — | 56 | — | | |
| Switching time | Turn-on time | t_{on} | $V_{DD} = -10 \text{ V}, I_D = -1.0 \text{ A},$ $V_{GS} = 0 \text{ to } -2.5 \text{ V}, R_G = 4.7 \Omega$ | — | 20 | — | ns |
| | Turn-off time | t_{off} | | — | 20 | — | |
| Drain-source forward voltage | V_{DSF} | $I_D = 1.8 \text{ A}, V_{GS} = 0$ (Note 3) | — | 0.85 | 1.2 | V | |

Note 3: Pulse test

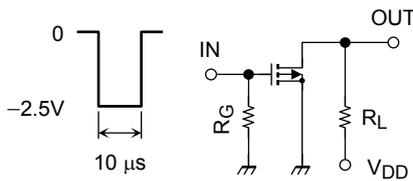
Q2 Electrical Characteristics (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit | |
|--------------------------------|---------------|---|---|------|---------|---------------|----|
| Drain-Source breakdown voltage | $V_{(BR)DSS}$ | $I_D = 0.1 \text{ mA}, V_{GS} = 0$ | 20 | — | — | V | |
| Drain cut-off current | I_{DSS} | $V_{DS} = 20 \text{ V}, V_{GS} = 0$ | — | — | 1 | μA | |
| Gate leakage current | I_{GSS} | $V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$ | — | — | ± 1 | μA | |
| Gate threshold voltage | V_{th} | $V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$ | 0.6 | — | 1.1 | V | |
| Forward transfer admittance | $ Y_{fs} $ | $V_{DS} = 3 \text{ V}, I_D = 10 \text{ mA}$ (Note 3) | 40 | — | — | mS | |
| Drain-Source on-resistance | $R_{DS(ON)}$ | $I_D = 10 \text{ mA}, V_{GS} = 4 \text{ V}$ (Note 3) | — | 1.5 | 3.0 | Ω | |
| | | $I_D = 10 \text{ mA}, V_{GS} = 2.5 \text{ V}$ (Note 3) | — | 2.2 | 4.0 | | |
| | | $I_D = 1 \text{ mA}, V_{GS} = 1.5 \text{ V}$ (Note 3) | — | 5.2 | 15 | | |
| Input capacitance | C_{iss} | $V_{DS} = 3 \text{ V}, V_{GS} = 0$ $f = 1 \text{ MHz}$ | — | 9.3 | — | pF | |
| Output capacitance | C_{oss} | | — | 9.8 | — | | |
| Reverse transfer capacitance | C_{rss} | | — | 4.5 | — | | |
| Switching time | Turn-on time | t_{on} | $V_{DD} = 3 \text{ V}, I_D = 10 \text{ mA},$ $V_{GS} = 0 \text{ to } 2.5 \text{ V}, R_G = 50 \Omega$ | — | 70 | — | ns |
| | Turn-off time | t_{off} | | — | 125 | — | |

Note 3: Pulse test

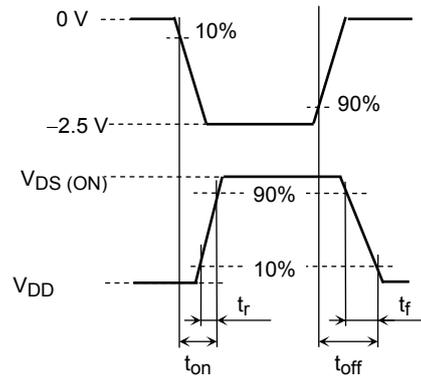
Switching Time Test Circuit (Q1)

(a) Test circuit



$V_{DD} = -10\text{ V}$
 $R_G = 4.7\ \Omega$
 Duty $\leq 1\%$
 V_{IN} : $t_r, t_f < 5\text{ ns}$
 Common Source
 $T_a = 25^\circ\text{C}$

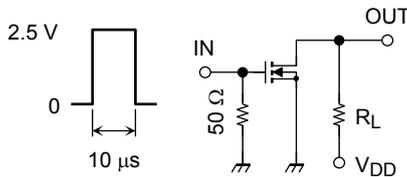
(b) V_{IN}



(c) V_{OUT}

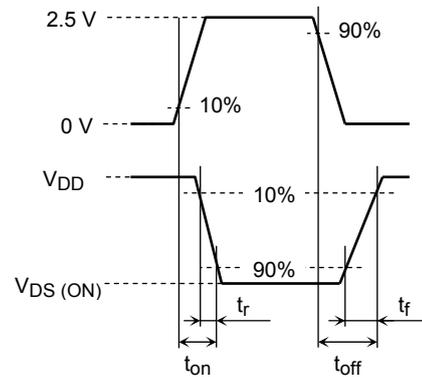
Switching Time Test Circuit (Q2)

(a) Test circuit



$V_{DD} = 3\text{ V}$
 Duty $\leq 1\%$
 V_{IN} : $t_r, t_f < 5\text{ ns}$
 ($Z_{out} = 50\ \Omega$)
 Common Source
 $T_a = 25^\circ\text{C}$

(b) V_{IN}



(c) V_{OUT}

Precaution(Pch)

V_{th} can be expressed as the voltage between the gate and source when the low operating current value is $I_D = -1\text{mA}$ for this product. For normal switching operation, $V_{GS(on)}$ requires a higher voltage than V_{th} and $V_{GS(off)}$ requires a lower voltage than V_{th} . (The relationship can be established as follows: $V_{GS(off)} < V_{th} < V_{GS(on)}$.)

Be sure to take this into consideration when using the device.

Precaution(Nch)

V_{th} can be expressed as the voltage between the gate and source when the low operating current value is $I_D = 0.1\text{mA}$ for this product. For normal switching operation, $V_{GS(on)}$ requires a higher voltage than V_{th} and $V_{GS(off)}$ requires a lower voltage than V_{th} . (The relationship can be established as follows: $V_{GS(off)} < V_{th} < V_{GS(on)}$.)

Be sure to take this into consideration when using the device.

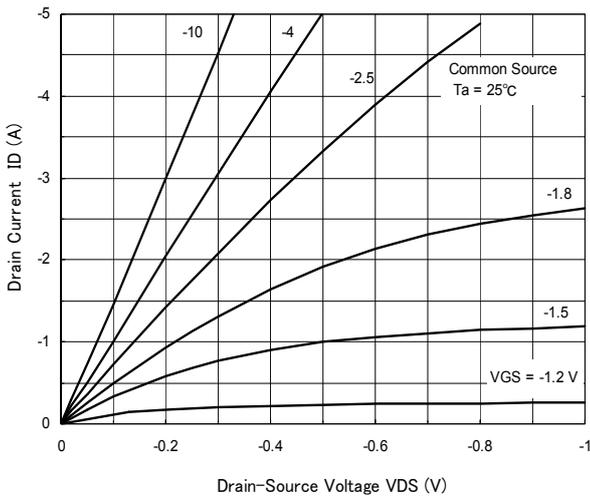
Handling Precaution

When handling individual devices (which are not yet mounted on a circuit board), ensure that the environment is protected against static electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

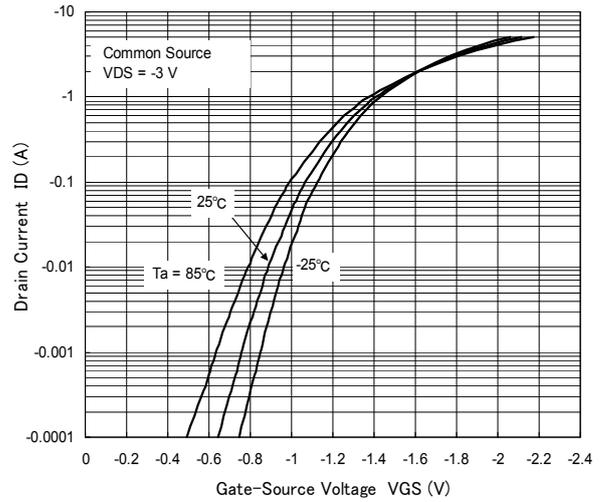
Thermal resistance $R_{th(j-a)}$ and drain power dissipation P_D vary depending on board material, board area, board thickness and pad area. When using this device, please take heat dissipation into consideration.

Q1 (Pch MOSFET)

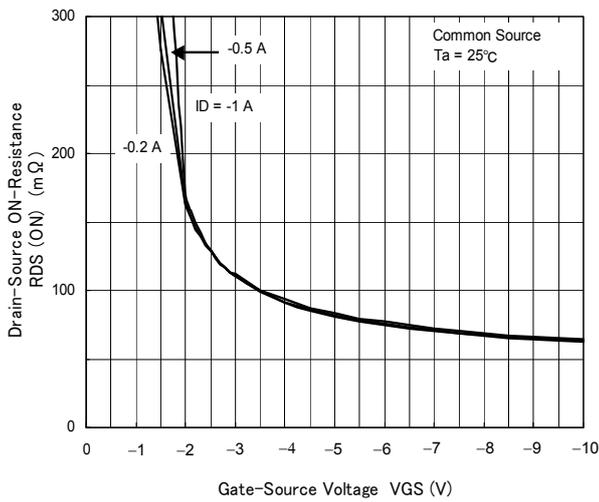
ID - VDS



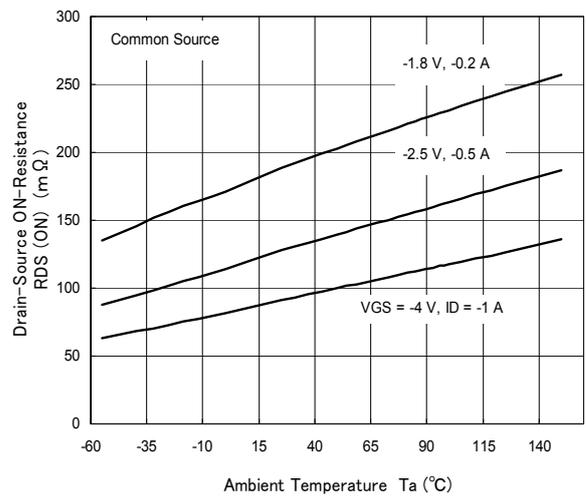
ID - VGS



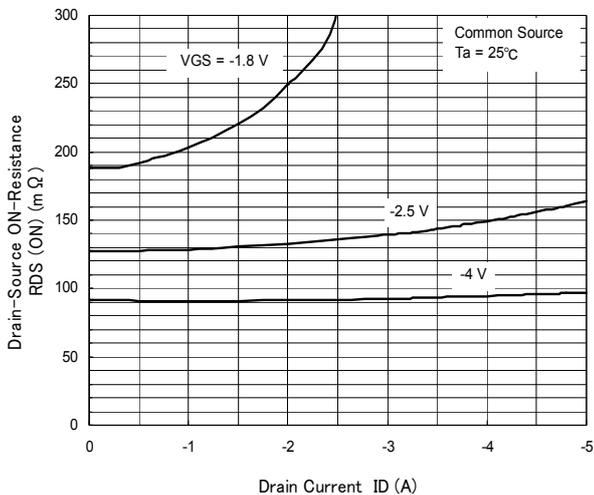
RDS (ON) - VGS



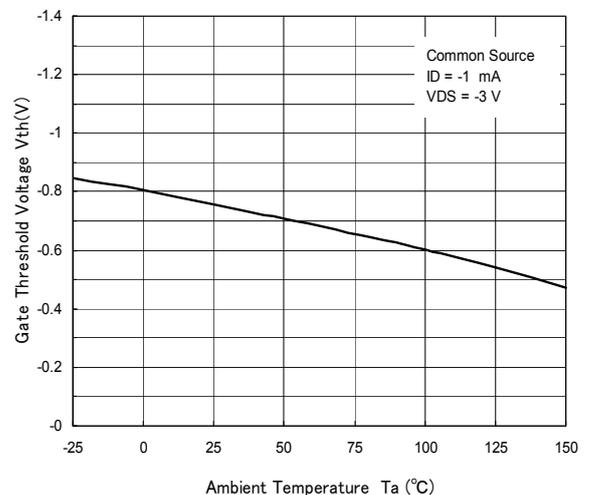
RDS (ON) - Ta



RDS (ON) - ID

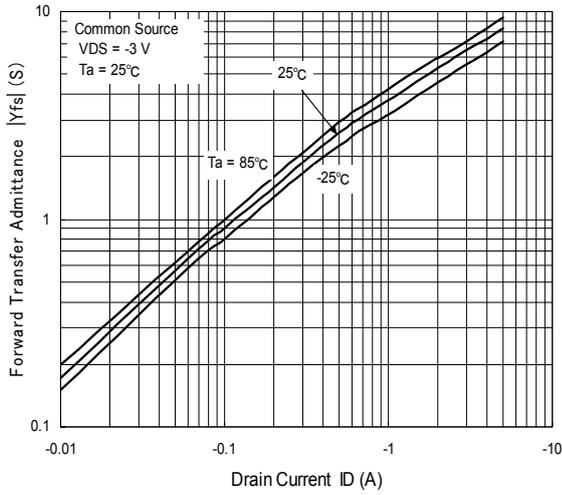


Vth - Ta

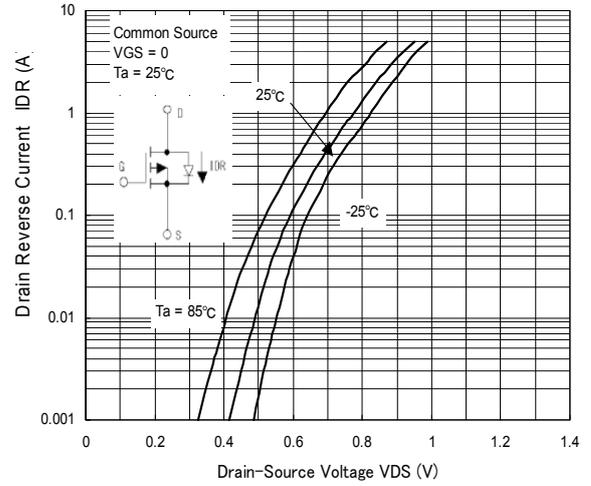


Q1 (Pch MOSFET)

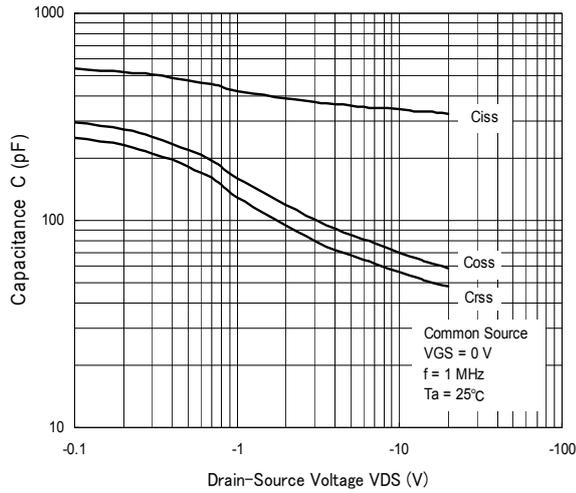
|Yfs| - ID



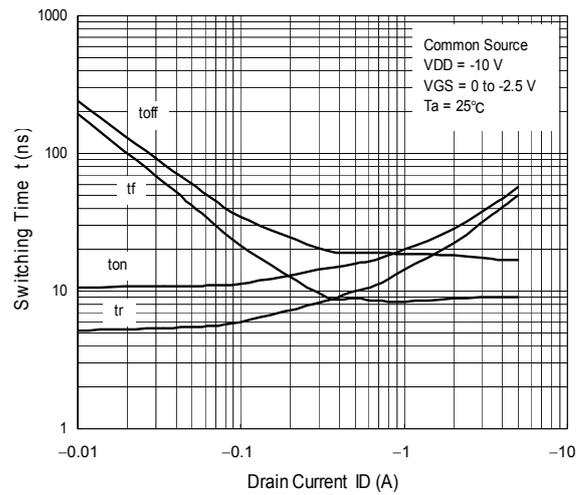
IDR - VDS



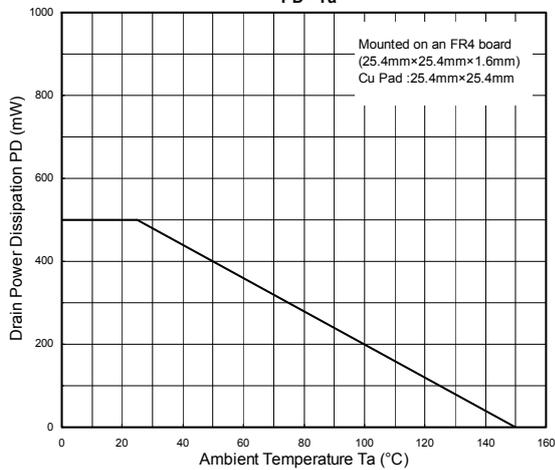
C - VDS



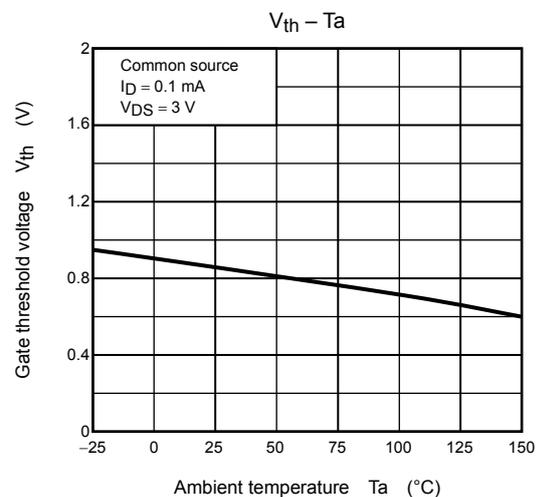
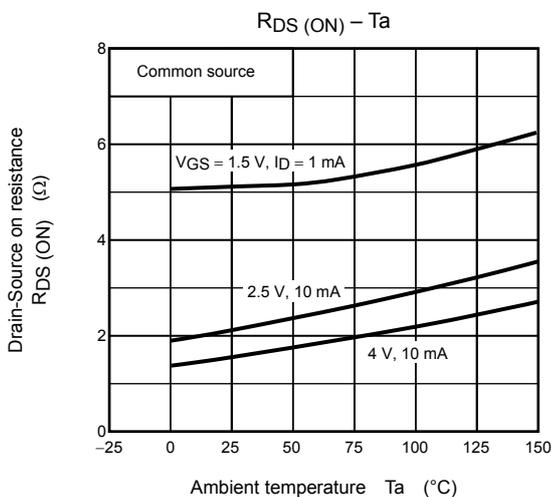
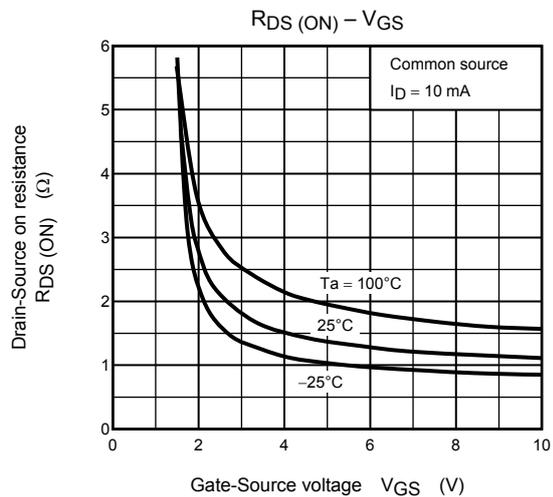
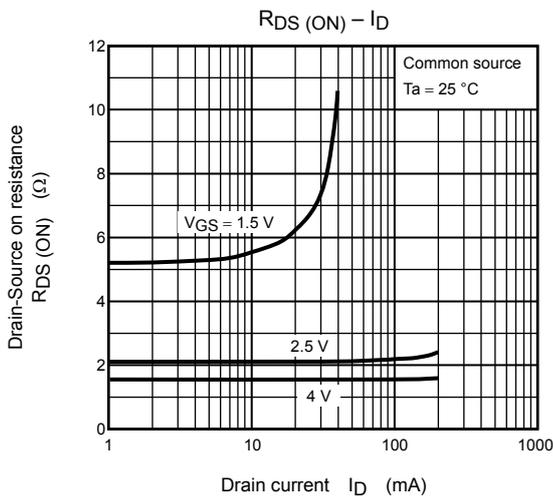
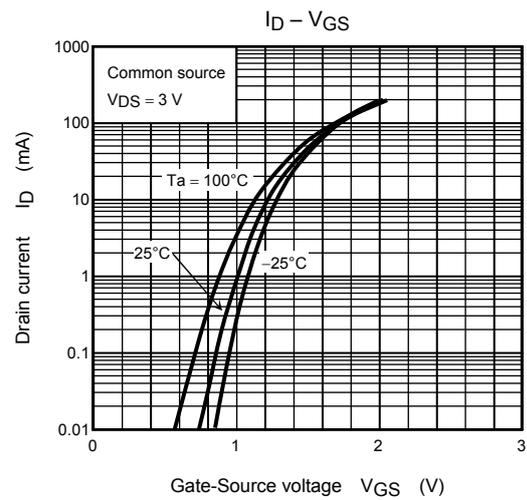
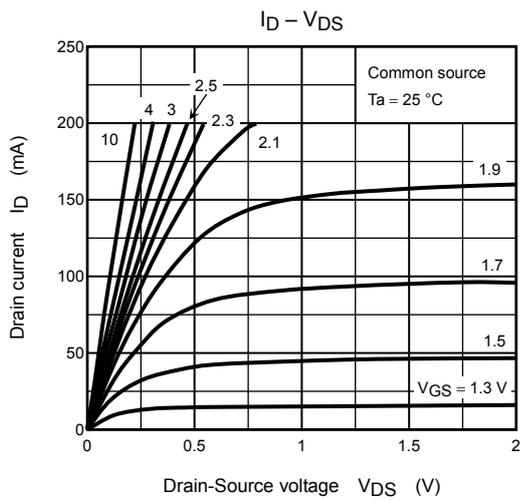
t - ID



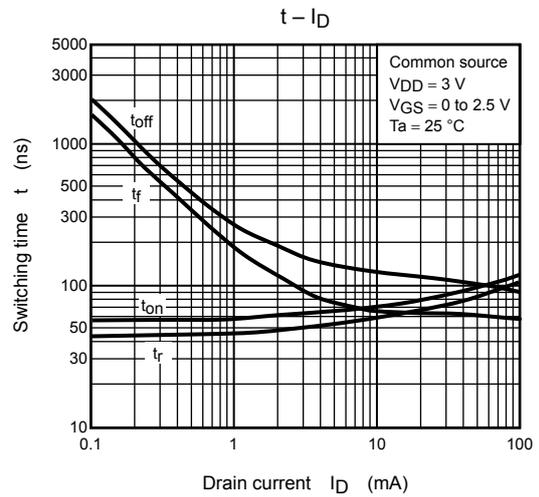
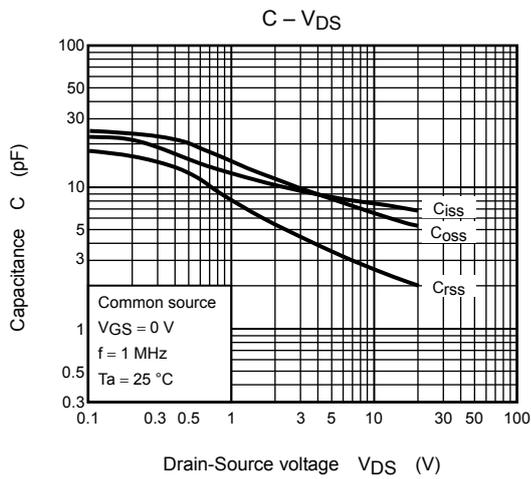
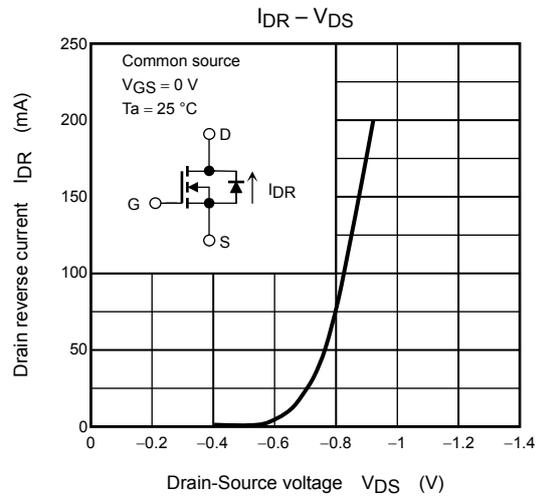
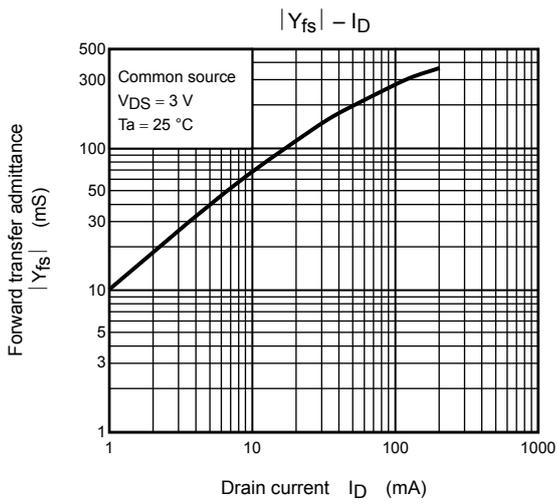
PD - Ta



Q2 (Nch MOSFET)



Q2 (Nch MOSFET)



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